

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE RECEIVED

In re Patent Application of: CROCE ET AL.

Serial No. 09/839,596

Confirmation No. 1496

Filing Date: April 20, 2001

For: RESURF LDMOS INTEGRATED

STRUCTURE

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TECHNOLOGY CENTER 2800

Examiner: O. Nadav

Art Unit: 2811

13/ Arrelt C ANDAMIO 1/18/03

RESPONSE TO NOTICE OF NON-COMPLIANT AMENDMENT

Director, U.S. Patent and Trademark Office Washington, D.C. 20231

Sir:

Responsive to the Notice of Non-Compliant Amendment mailed on December 10, 2002, please enter the amendments and remarks set out below.

In the Claims:

Please amend Claim 14 as follows:

- 14. (Amended) A lateral diffused metal oxide semiconductor (LDMOS) integrated device comprising:
 - a semiconductor substrate;

a drain region of a first conductivity type adjacent said semiconductor substrate and comprising a superficial buffer region being more heavily doped than adjacent portions of said drain region;

said superficial buffer region having a dopant concentration of about 5×10^{16} to 5×10^{17} atoms cm⁻³ and the adjacent portions of said drain region having a dopant concentration of about 2.5×10^{15} to 2.5×10^{16} atoms cm⁻³;

- a body region surrounded by said superficial buffer region and having a second conductivity type; and
 - a source region in said body region and having the